# 25–29 GHz GaAs MMIC Driver Amplifier



AA026P1-00

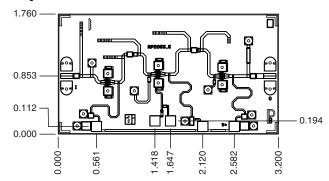
#### **Features**

- Single Bias Supply Operation (6 V)
- 17 dB Typical Small Signal Gain
- 16 dBm Typical P<sub>1 dB</sub> Output Power at 26.5 GHz
- 0.25 µm Ti/Pd/Au Gates
- 100% On-Wafer RF and DC Testing
- 100% Visual Inspection to MIL-STD-883 MT 2010

#### **Description**

Skyworks' three-stage reactively-matched 25–29 GHz GaAs MMIC driver amplifier has typical small signal gain of 17 dB with a typical  $P_{1\ dB}$  of 16 dBm at 26.5 GHz. The chip uses Skyworks' proven 0.25  $\mu m$  MESFET technology, and is based upon MBE layers and electron beam lithography for the highest uniformity and repeatability. The FETs employ surface passivation to ensure a rugged, reliable part with through-substrate via holes and gold-based backside metallization to facilitate a conductive epoxy die attach process. All chips are screened for gain, output power and S-parameters prior to shipment for guaranteed performance.

## **Chip Outline**



Dimensions indicated in mm. All DC (V) pads are  $0.1 \times 0.1 \text{ mm}$  and RF In, Out pads are 0.07 mm wide. Chip thickness = 0.1 mm.

## **Absolute Maximum Ratings**

Characteristic	Value	
Operating Temperature (T <sub>C</sub> )	-55°C to +90°C	
Storage Temperature (T <sub>ST</sub> )	-65°C to +150°C	
Bias Voltage (V <sub>D</sub> )	7 V <sub>DC</sub>	
Power In (P <sub>IN</sub> )	16 dBm	
Junction Temperature (T <sub>J</sub> )	175°C	

## Electrical Specifications at 25°C (V<sub>DS</sub> = 6 V)

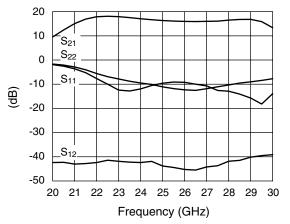
Parameter	Condition	Symbol	Min.	Typ. <sup>3</sup>	Max.	Unit
Drain Current		I <sub>DS</sub>		120	170	mA
Small Signal Gain	F = 25–29 GHz	G	14	17		dB
Input Return Loss	F = 25–29 GHz	RLI		-8	-6	dB
Output Return Loss	F = 25–29 GHz	RLO		-10	-6	dB
Output Power at 1 dB Gain Compression	F = 26.5 GHz	P <sub>1 dB</sub>	14	16		dBm
Saturated Output Power	F = 26.5 GHz	P <sub>SAT</sub>	15	17		dBm
Two-Tone Output Third-Order Intercept <sup>1</sup>	F = 26.5 GHz	OIP3		24.5		dBm
Thermal Resistance <sup>2</sup>		Θ <sub>JC</sub>		132		°C/W

<sup>1.</sup> Not measured on a 100% basis.

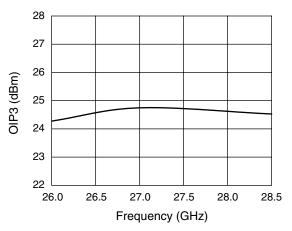
<sup>2.</sup> Calculated value based on measurement of discrete FET.

<sup>3.</sup> Typical represents the median parameter value across the specified frequency range for the median chip.

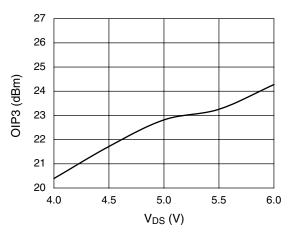
## **Typical Performance Data**



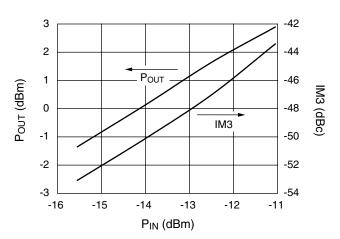
Typical Small Signal Performance S-Parameters  $(V_D = 6 V)$ 



Two-Tone Output Third-Order Intercept @ V<sub>DS</sub> = 6 V

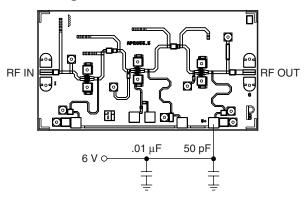


Two-Tone Output Third-Order Intercept @ 26 GHz



Output Power and Relative Third-Order Intermodulation Products
F = 26 GHz, V<sub>DS</sub> = 6 V

## **Bias Arrangement**



For biasing on, adjust  $V_{DS}$  from zero to the desired value (6 V recommended). For biasing off, reverse the biasing on procedure.

## **Circuit Schematic**

